

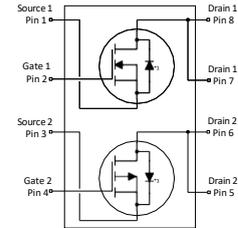
## 英飞凌 MOSFET

PG-DSO-8

OptiMOS™ 3 功率场效应管，40 V

### 特性

- 互补型 N 沟道和 P 沟道
- 极低的导通电阻  $R_{DS(on)}$
- 卓越的热阻抗
- 100% 雪崩测试
- 无铅镀层；符合 RoHS 标准
- 符合 IEC61249-2-21 标准的无卤素

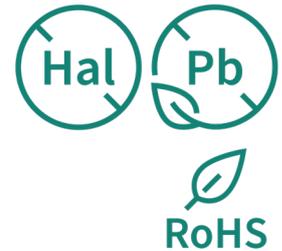


### 产品验证

符合 JEDEC 标准

表 1 主要性能参数

Parameter	Value	Unit
$V_{DS}$ (n-channel)	40	V
$R_{DS(on),max}$ (n-channel)	17	m $\Omega$
$I_D$ (n-channel)	9.6	A
$V_{DS}$ (p-channel)	-40	V
$R_{DS(on),max}$ (p-channel)	23	m $\Omega$
$I_D$ (p-channel)	-8.8	A



Type/Ordering Code	Package	Marking	Related Links
ISA170230C04LMDS	PG-DSO-8	1723C04L	-

本数据手册的原文使用英文撰写。为方便起见，英飞凌提供了译文；由于翻译过程中可能使用了自动化工具，英飞凌不保证译文的准确性。为确保准确性，请务必访问 [infineon.com](https://www.infineon.com) 参考最新的英文版本（控制文档）。

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## 1 最大额定值

除非另有规定,  $T_A=25^\circ\text{C}$

表 2 最大额定值 (N 沟道)

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Continuous drain current <sup>1)</sup>	$I_D$	-	-	9.6 6.1 5.2 7.2	A	$V_{GS}=10\text{ V}, T_C=25^\circ\text{C}$ $V_{GS}=10\text{ V},$ $T_C=100^\circ\text{C}$ $V_{GS}=4.5\text{ V}, T_C=100^\circ\text{C}$ $V_{GS}=10\text{ V}, T_A=25^\circ\text{C}, R_{thJA}=90^\circ\text{C/W}$ <sup>2)</sup>
Pulsed drain current <sup>3)</sup>	$I_{D,pulse}$	-	-	38	A	$T_A=25^\circ\text{C}$
Avalanche energy, single pulse <sup>4)</sup>	$E_{AS}$	-	-	36	mJ	$I_D=9.6\text{ A}, R_{GS}=25\ \Omega$
Gate source voltage	$V_{GS}$	-20	-	20	V	-
Power dissipation	$P_{tot}$	-	-	2.5 1.4	W	$T_C=25^\circ\text{C}$ $T_A=25^\circ\text{C}, R_{thJA}=90^\circ\text{C/W}$ <sup>2)</sup>
Operating and storage temperature	$T_j, T_{stg}$	-55	-	150	$^\circ\text{C}$	-

- 1) 额定值指产品仅具有数据手册指定的绝对最大值, 保持外壳温度符合规定要求。其他情况下的温度, n 沟道请参见图 2, p 沟道请参见图 17。需要根据实际环境条件降低等级。
- 2) 器件置于  $40\text{ mm} \times 40\text{ mm} \times 1.5\text{ mm}$  环氧树脂印刷电路板 FR4 上, 配有  $6\text{ cm}^2$  (单层,  $70\ \mu\text{m}$  厚) 铜层面积用于漏极连接。印刷电路板垂直放置在静止空气中。一个开关管工作。
- 3) 详细信息请参见图 3 与 18
- 4) 详细信息请参见图 13 与 28

表 3 最大额定值 (P 沟道)

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Continuous drain current <sup>5)</sup>	$I_D$	-	-	-8.8 -5.6 -4.9 -6.6	A	$V_{GS}=-10\text{ V}, T_C=25^\circ\text{C}$ $V_{GS}=-10\text{ V},$ $T_C=100^\circ\text{C}$ $V_{GS}=-4.5\text{ V}, T_C=100^\circ\text{C}$ $V_{GS}=-10\text{ V}, T_A=25^\circ\text{C}, R_{thJA}=90^\circ\text{C/W}$ <sup>6)</sup>
Pulsed drain current <sup>7)</sup>	$I_{D,pulse}$	-	-	-35	A	$T_A=25^\circ\text{C}$
Avalanche energy, single pulse <sup>8)</sup>	$E_{AS}$	-	-	36	mJ	$I_D=-8.8\text{ A}, R_{GS}=25\ \Omega$
Gate source voltage	$V_{GS}$	-20	-	20	V	-
Power dissipation	$P_{tot}$	-	-	2.5 1.4	W	$T_C=25^\circ\text{C}$ $T_A=25^\circ\text{C}, R_{thJA}=90^\circ\text{C/W}$ <sup>6)</sup>
Operating and storage temperature	$T_j, T_{stg}$	-55	-	150	$^\circ\text{C}$	-

- 5) 额定值指产品仅具有数据手册指定的绝对最大值, 保持外壳温度符合规定要求。其他情况下的温度, n 沟道请参见图 2, p 沟道请参见图 17。需要根据实际环境条件降低等级。
- 6) 器件置于  $40\text{ mm} \times 40\text{ mm} \times 1.5\text{ mm}$  环氧树脂印刷电路板 FR4 上, 配有  $6\text{ cm}^2$  (单层,  $70\ \mu\text{m}$  厚) 铜层面积用于漏极连接。印刷电路板

**Public**

# OptiMOS™ 3 Power-Transistors, 40V

ISA170230C04LMDS

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垂直放置在静止空气中。一个开关管工作。

**Public**

# OptiMOS™ 3 Power-Transistors, 40V

ISA170230C04LMDS

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- 7) 详细信息请参见图 3 与18
- 8) 详细信息请参见图 13 与28

## 2 热特性

表 4 热特性

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - solder point	$R_{thJC}$	-	-	50	°C/W	-
Thermal resistance, junction - ambient, minimal footprint, steady state	$R_{thJA}$	-	-	150	°C/W	-
Thermal resistance, junction - ambient, 6 cm <sup>2</sup> cooling area, steady state <sup>9)</sup>	$R_{thJA}$	-	-	90	°C/W	-

<sup>9)</sup> 器件置于40 mm × 40 mm × 1.5 mm 环氧树脂印刷电路板 FR4 上，配有6 cm<sup>2</sup>（单层，70 μm厚）铜层面积用于漏极连接。印刷电路板垂直放置在静止空气中。一个开关管工作。

### 3 电气特性

除非另有规定,  $T_j=25\text{ }^\circ\text{C}$

表 5 静态特性 (N 沟道)

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	40	-	-	V	$V_{GS}=0\text{ V}, I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	1.1	-	2.7	V	$V_{DS}=V_{GS}, I_D=1000\text{ }\mu\text{A}$
Zero gate voltage drain current	$I_{DSS}$	-	0.1 10	1 100	$\mu\text{A}$	$V_{DS}=40\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ }^\circ\text{C}$ $V_{DS}=40\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ }^\circ\text{C}$
Gate-source leakage current	$I_{GSS}$	-	10	100	nA	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	13 18	17 23.6	$\text{m}\Omega$	$V_{GS}=10\text{ V}, I_D=9.6\text{ A}$ $V_{GS}=4.5\text{ V}, I_D=8.5\text{ A}$
Gate resistance	$R_G$	-	1.1	-	$\Omega$	-
Transconductance <sup>10)</sup>	$g_{fs}$	12	25	-	S	$ V_{DS} \geq 2 I_D R_{DS(on)max}, I_D=9.6\text{ A}$

<sup>10)</sup> 由设计指定, 未经过生产测试。

表 6 静态特性 (P 沟道)

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	-40	-	-	V	$V_{GS}=0\text{ V}, I_D=-1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	-1.1	-	-2.7	V	$V_{DS}=V_{GS}, I_D=-1000\text{ }\mu\text{A}$
Zero gate voltage drain current	$I_{DSS}$	-	-0.1 -10	-1 -100	$\mu\text{A}$	$V_{DS}=-40\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ }^\circ\text{C}$ $V_{DS}=-40\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ }^\circ\text{C}$
Gate-source leakage current	$I_{GSS}$	-	-10	-100	nA	$V_{GS}=-20\text{ V}, V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	18 23	23 29.5	$\text{m}\Omega$	$V_{GS}=-10\text{ V}, I_D=-8.8\text{ A}$ $V_{GS}=-4.5\text{ V}, I_D=-6.9\text{ A}$
Gate resistance	$R_G$	-	3	-	$\Omega$	-
Transconductance <sup>11)</sup>	$g_{fs}$	12	24	-	S	$ V_{DS} \geq 2 I_D R_{DS(on)max}, I_D=-8.8\text{ A}$

<sup>11)</sup> 由设计指定, 未经过生产测试。

表 7 动态特性 (N 沟道)

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Input capacitance <sup>12)</sup>	$C_{iss}$	-	880	1100	pF	$V_{GS}=0\text{ V}, V_{DS}=20\text{ V}, f=1\text{ MHz}$
Output capacitance <sup>12)</sup>	$C_{oss}$	-	220	290	pF	$V_{GS}=0\text{ V}, V_{DS}=20\text{ V}, f=1\text{ MHz}$
Reverse transfer capacitance <sup>12)</sup>	$C_{rss}$	-	15	26	pF	$V_{GS}=0\text{ V}, V_{DS}=20\text{ V}, f=1\text{ MHz}$

Turn-on delay time	$t_{d(on)}$	-	6.7	-	ns	$V_{DD}=20\text{ V}, V_{GS}=4.5\text{ V}, I_D=9.6\text{ A},$ $R_{G,ext}=1.6\ \Omega$
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表 7 动态特性 (N 沟道)

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Rise time	$t_r$	-	5.0	-	ns	$V_{DD}=20\text{ V}$ , $V_{GS}=4.5\text{ V}$ , $I_D=9.6\text{ A}$ , $R_{G,ext}=1.6\ \Omega$
Turn-off delay time	$t_{d(off)}$	-	4.6	-	ns	$V_{DD}=20\text{ V}$ , $V_{GS}=4.5\text{ V}$ , $I_D=9.6\text{ A}$ , $R_{G,ext}=1.6\ \Omega$
Fall time	$t_f$	-	4.0	-	ns	$V_{DD}=20\text{ V}$ , $V_{GS}=4.5\text{ V}$ , $I_D=9.6\text{ A}$ , $R_{G,ext}=1.6\ \Omega$
Gate to source charge	$Q_{gs}$	-	2.7	-	nC	$V_{DD}=20\text{ V}$ , $I_D=9.6\text{ A}$ , $V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	1.5	-	nC	$V_{DD}=20\text{ V}$ , $I_D=9.6\text{ A}$ , $V_{GS}=0\text{ to }4.5\text{ V}$
Gate to drain charge	$Q_{gd}$	-	1.6	-	nC	$V_{DD}=20\text{ V}$ , $I_D=9.6\text{ A}$ , $V_{GS}=0\text{ to }4.5\text{ V}$
Switching charge	$Q_{sw}$	-	2.8	-	nC	$V_{DD}=20\text{ V}$ , $I_D=9.6\text{ A}$ , $V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge total <sup>12)</sup>	$Q_g$	-	6.0	9.0	nC	$V_{DD}=20\text{ V}$ , $I_D=9.6\text{ A}$ , $V_{GS}=0\text{ to }4.5\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	3.1	-	V	$V_{DD}=20\text{ V}$ , $I_D=9.6\text{ A}$ , $V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge total	$Q_g$	-	13	19.5	nC	$V_{DD}=20\text{ V}$ , $I_D=9.6\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Output charge	$Q_{oss}$	-	7.8	-	nC	$V_{DS}=20\text{ V}$ , $V_{GS}=0\text{ V}$

<sup>12)</sup> 由设计指定, 未经过生产测试。

表 8 动态特性 (P 沟道)

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Input capacitance <sup>13)</sup>	$C_{iss}$	-	1900	2500	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=-20\text{ V}$ , $f=1\text{ MHz}$
Output capacitance <sup>13)</sup>	$C_{oss}$	-	750	980	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=-20\text{ V}$ , $f=1\text{ MHz}$
Reverse transfer capacitance <sup>13)</sup>	$C_{rss}$	-	38	67	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=-20\text{ V}$ , $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	15	-	ns	$V_{DD}=-20\text{ V}$ , $V_{GS}=-4.5\text{ V}$ , $I_D=-8.8\text{ A}$ , $R_{G,ext}=1.6\ \Omega$
Rise time	$t_r$	-	8.9	-	ns	$V_{DD}=-20\text{ V}$ , $V_{GS}=-4.5\text{ V}$ , $I_D=-8.8\text{ A}$ , $R_{G,ext}=1.6\ \Omega$
Turn-off delay time	$t_{d(off)}$	-	15	-	ns	$V_{DD}=-20\text{ V}$ , $V_{GS}=-4.5\text{ V}$ , $I_D=-8.8\text{ A}$ , $R_{G,ext}=1.6\ \Omega$
Fall time	$t_f$	-	7.4	-	ns	$V_{DD}=-20\text{ V}$ , $V_{GS}=-4.5\text{ V}$ , $I_D=-8.8\text{ A}$ , $R_{G,ext}=1.6\ \Omega$
Gate to source charge	$Q_{gs}$	-	-5.9	-	nC	$V_{DD}=-20\text{ V}$ , $I_D=-8.8\text{ A}$ , $V_{GS}=0\text{ to }-4.5\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	-3.3	-	nC	$V_{DD}=-20\text{ V}$ , $I_D=-8.8\text{ A}$ , $V_{GS}=0\text{ to }-4.5\text{ V}$
Gate to drain charge	$Q_{gd}$	-	-3.5	-	nC	$V_{DD}=-20\text{ V}$ , $I_D=-8.8\text{ A}$ , $V_{GS}=0\text{ to }-4.5\text{ V}$
Switching charge	$Q_{sw}$	-	-6.1	-	nC	$V_{DD}=-20\text{ V}$ , $I_D=-8.8\text{ A}$ , $V_{GS}=0\text{ to }-4.5\text{ V}$

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Gate charge total <sup>13)</sup>	$Q_g$	-	-12.6	-19	nC	$V_{DD}=-20\text{ V}, I_D=-8.8\text{ A}, V_{GS}=0\text{ to }-4.5\text{ V}$
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表 8 动态特性 (P 沟道)

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Gate plateau voltage	$V_{\text{plateau}}$	-	-3.1	-	V	$V_{\text{DD}}=-20\text{ V}$ , $I_{\text{D}}=-8.8\text{ A}$ , $V_{\text{GS}}=0$ to $-4.5\text{ V}$
Gate charge total <sup>13)</sup>	$Q_{\text{g}}$	-	-25	-38	nC	$V_{\text{DD}}=-20\text{ V}$ , $I_{\text{D}}=-8.8\text{ A}$ , $V_{\text{GS}}=0$ to $-10\text{ V}$
Output charge	$Q_{\text{oss}}$	-	-22	-	nC	$V_{\text{DS}}=-20\text{ V}$ , $V_{\text{GS}}=0\text{ V}$

<sup>13)</sup> 由设计指定, 未经过生产测试。

表 9 反向二极管 (N 沟道)

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	$I_{\text{S}}$	-	-	3.1	A	$T_{\text{C}}=25\text{ °C}$
Diode pulse current	$I_{\text{S,pulse}}$	-	-	38	A	$T_{\text{A}}=25\text{ °C}$
Diode forward voltage	$V_{\text{SD}}$	-	0.86	1	V	$V_{\text{GS}}=0\text{ V}$ , $I_{\text{F}}=9.6\text{ A}$ , $T_{\text{j}}=25\text{ °C}$
Reverse recovery time	$t_{\text{rr}}$	-	13	-	ns	$V_{\text{R}}=20\text{ V}$ , $I_{\text{F}}=9.6\text{ A}$ , $di_{\text{F}}/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	$Q_{\text{rr}}$	-	4.3	-	nC	$V_{\text{R}}=20\text{ V}$ , $I_{\text{F}}=9.6\text{ A}$ , $di_{\text{F}}/dt=100\text{ A}/\mu\text{s}$

表 10 反向二极管 (P 沟道)

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	$I_{\text{S}}$	-	-	-3.4	A	$T_{\text{C}}=25\text{ °C}$
Diode pulse current	$I_{\text{S,pulse}}$	-	-	-35	A	$T_{\text{A}}=25\text{ °C}$
Diode forward voltage	$V_{\text{SD}}$	-	-0.86	-1	V	$V_{\text{GS}}=0\text{ V}$ , $I_{\text{F}}=-8.8\text{ A}$ , $T_{\text{j}}=25\text{ °C}$
Reverse recovery time	$t_{\text{rr}}$	-	22	-	ns	$V_{\text{R}}=-20\text{ V}$ , $I_{\text{F}}=-8.8\text{ A}$ , $di_{\text{F}}/dt=-100\text{ A}/\mu\text{s}$
Reverse recovery charge	$Q_{\text{rr}}$	-	11	-	nC	$V_{\text{R}}=-20\text{ V}$ , $I_{\text{F}}=-8.8\text{ A}$ , $di_{\text{F}}/dt=-100\text{ A}/\mu\text{s}$

## 4 电气特性图

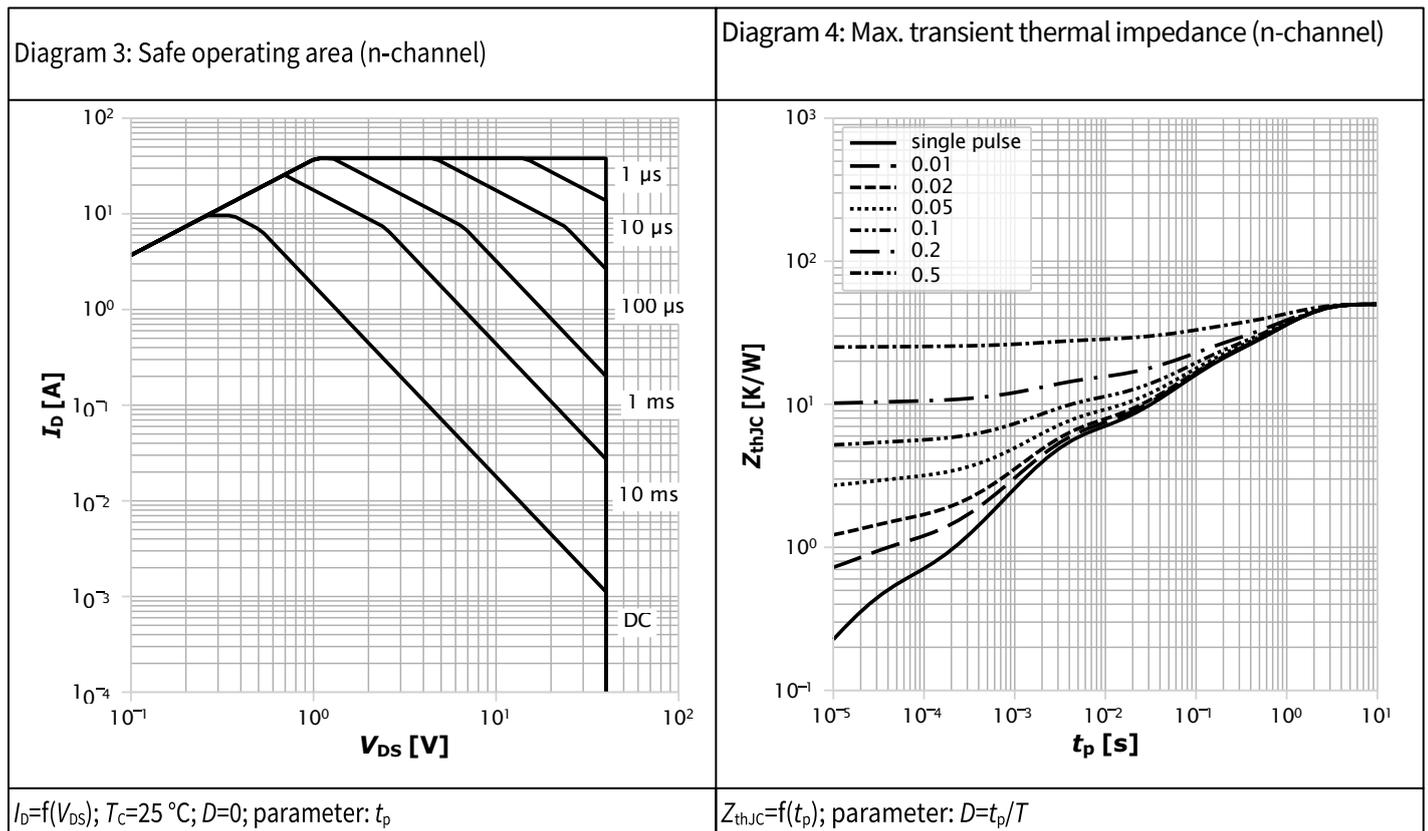
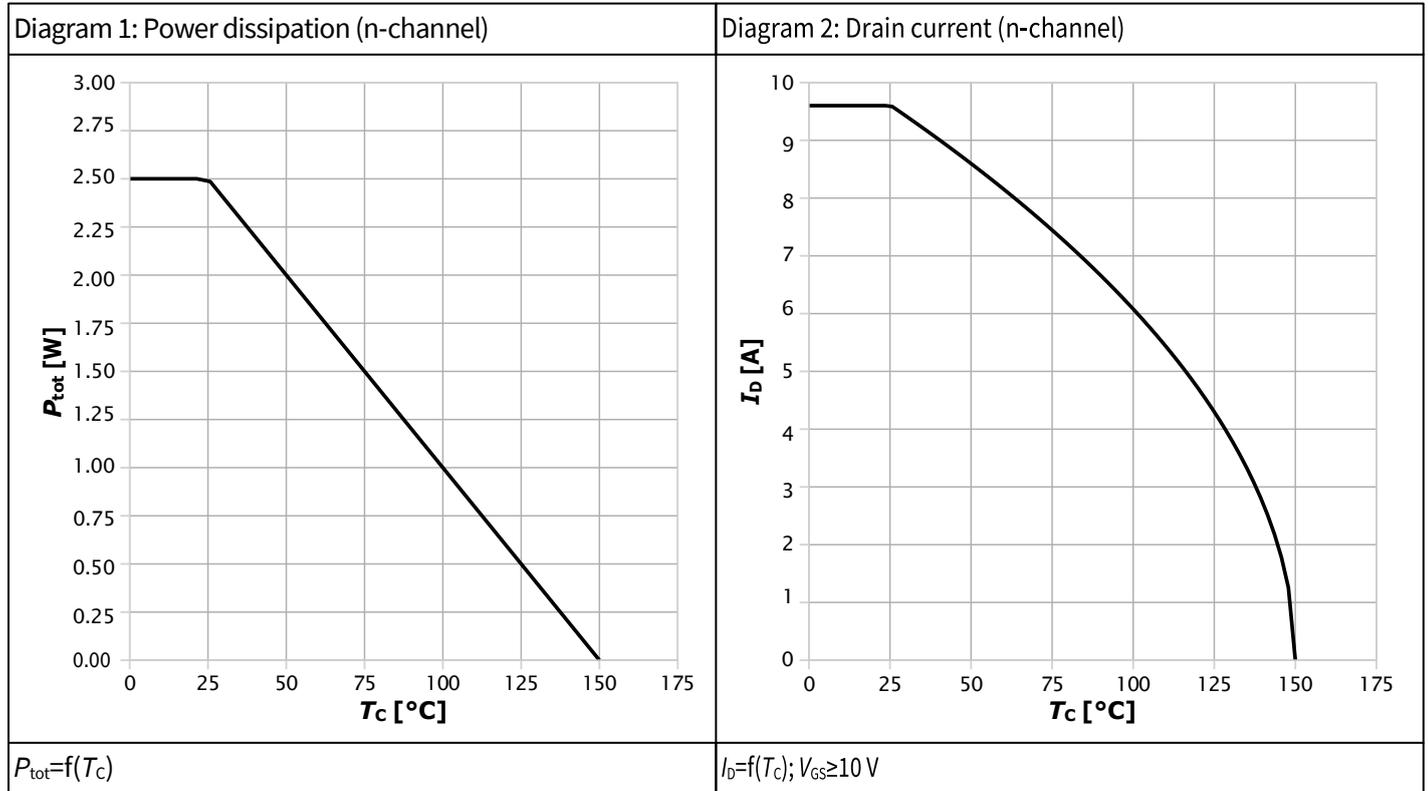
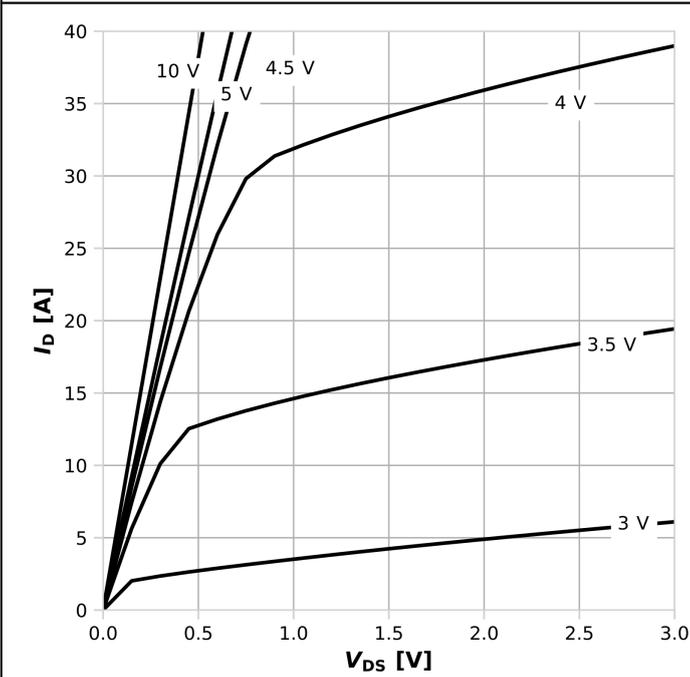
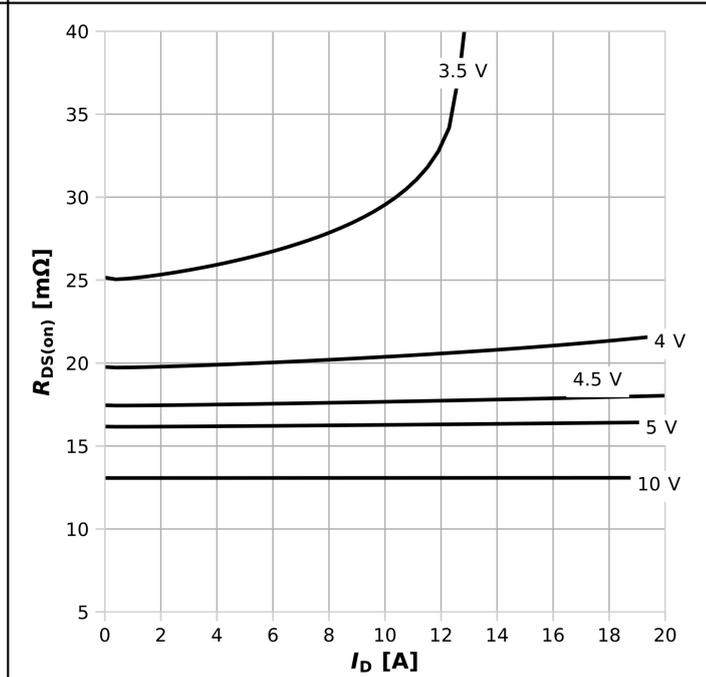


Diagram 5: Typ. output characteristics (n-channel)



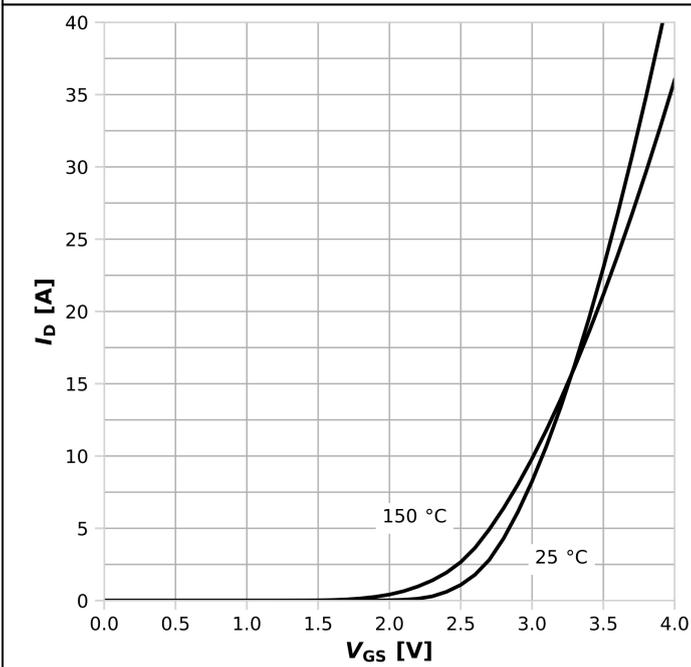
$I_D = f(V_{DS})$ ,  $T_j = 25^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 6: Typ. drain-source on resistance (n-channel)



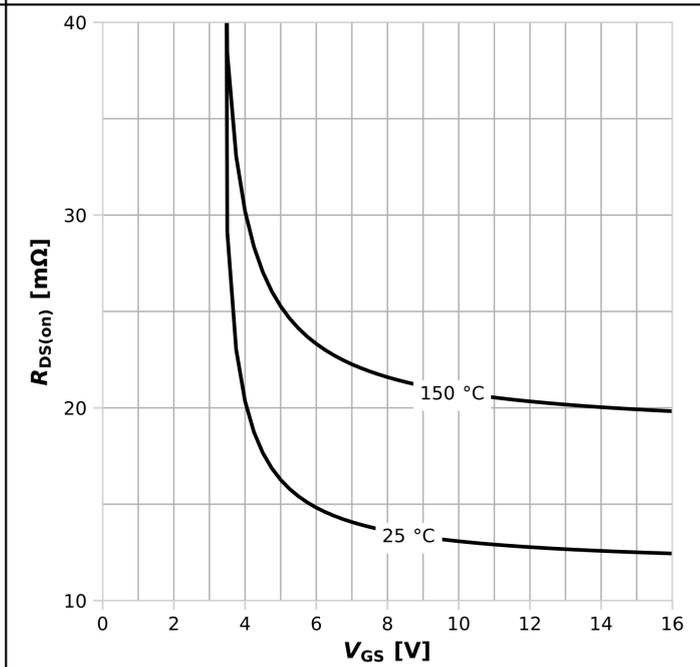
$R_{DS(on)} = f(I_D)$ ,  $T_j = 25^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 7: Typ. transfer characteristics (n-channel)



$I_D = f(V_{GS}), |V_{DS}| > 2|I_D|R_{DS(on)max}$ ; parameter:  $T_j$

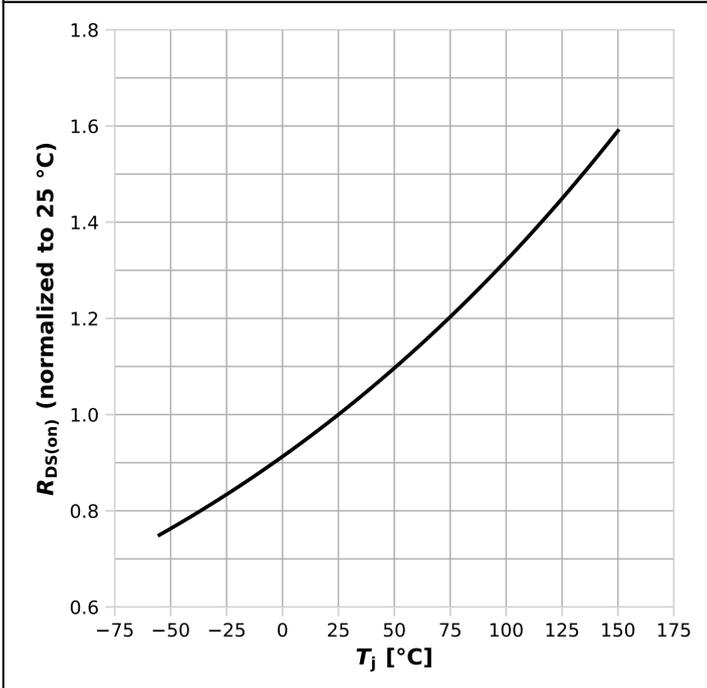
Diagram 8: Typ. drain-source on resistance (n-channel)



$R_{DS(on)} = f(V_{GS}), I_D = 9.6 \text{ A}$ ; parameter:  $T_j$

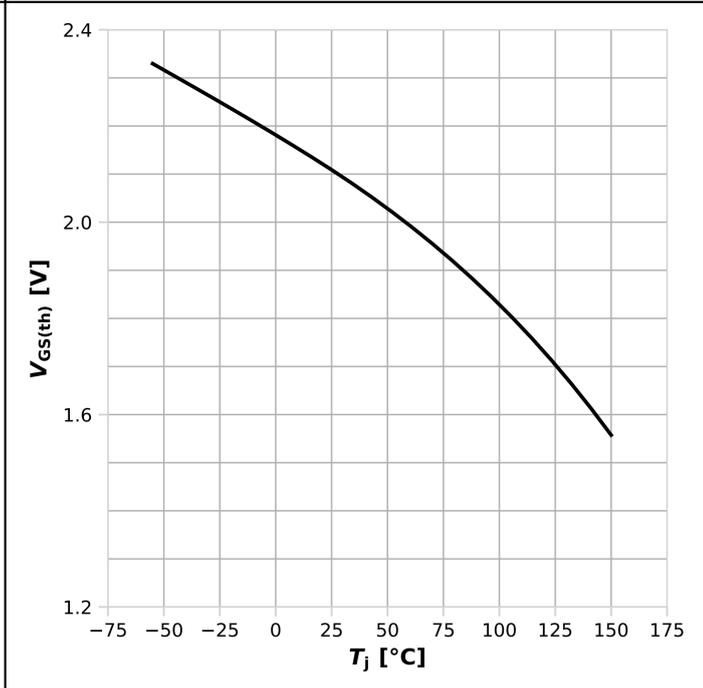


Diagram 9: Normalized drain-source on resistance (n-channel)



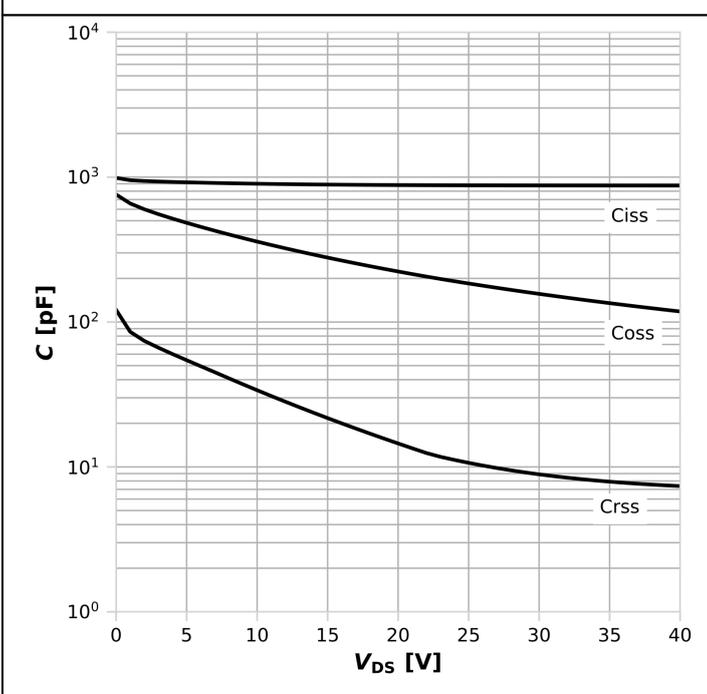
$R_{DS(on)}=f(T_j)$ ,  $I_D=9.6$  A,  $V_{GS}=10$  V

Diagram 10: Typ. gate threshold voltage (n-channel)



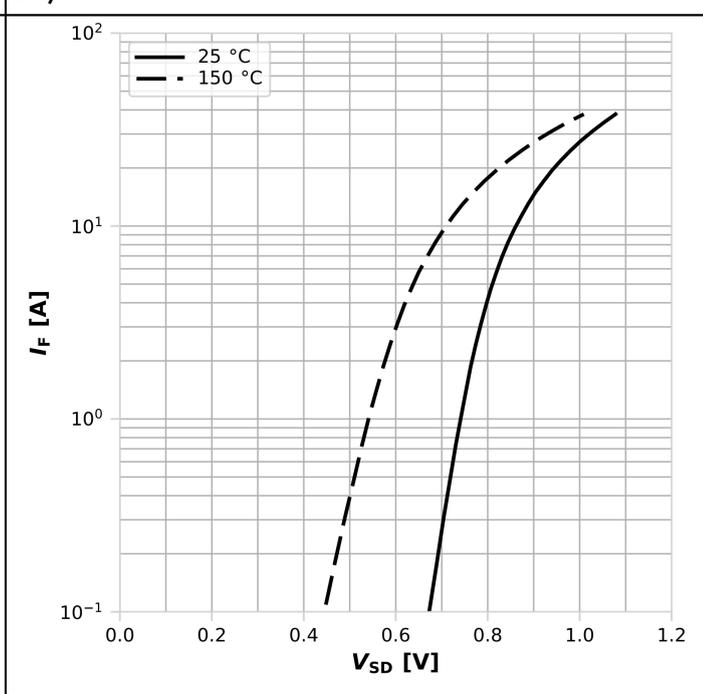
$V_{GS(th)}=f(T_j)$ ,  $V_{GS}=V_{DS}$ ; parameter:  $I_D=1000\mu$ A

Diagram 11: Typ. capacitances (n-channel)



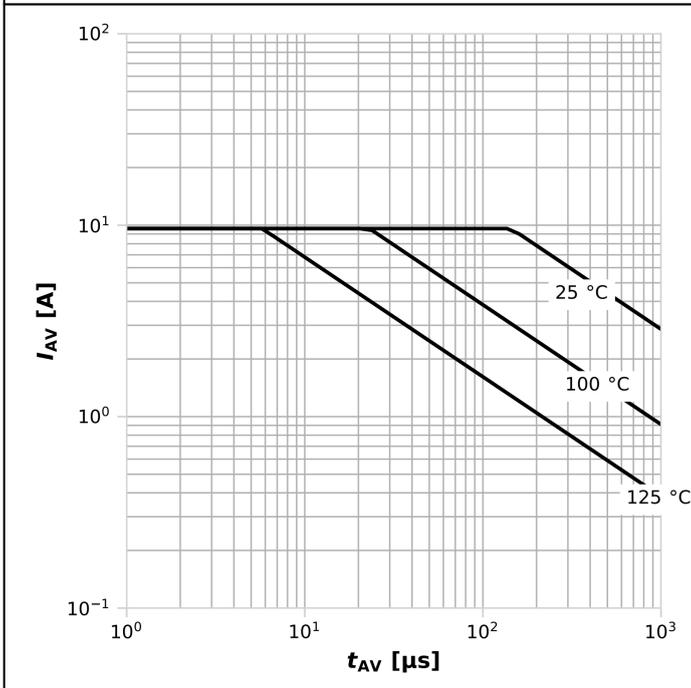
$C=f(V_{DS})$ ;  $V_{GS}=0$  V;  $f=1$  MHz

Diagram 12: Forward characteristics of reverse diode (n-ch.)



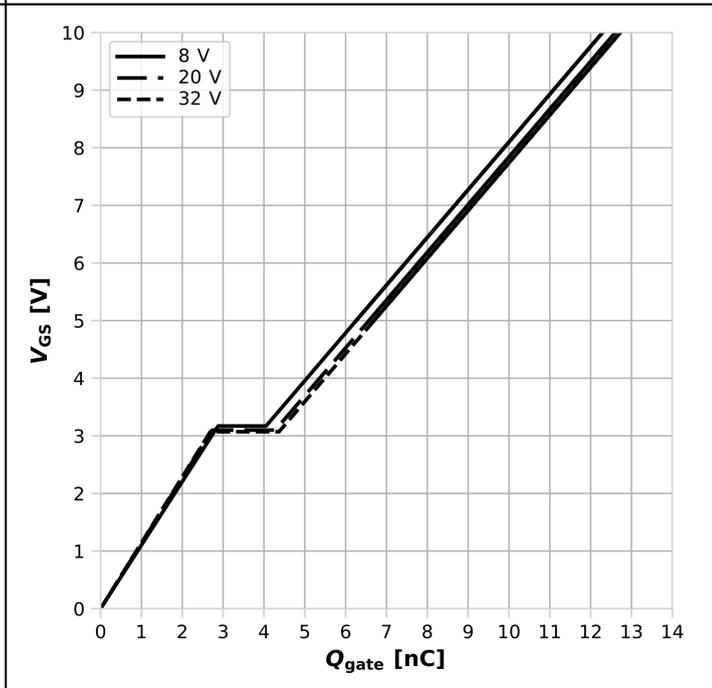
$I_F=f(V_{SD})$ ; parameter:  $T_j$

Diagram 13: Avalanche characteristics (n-channel)



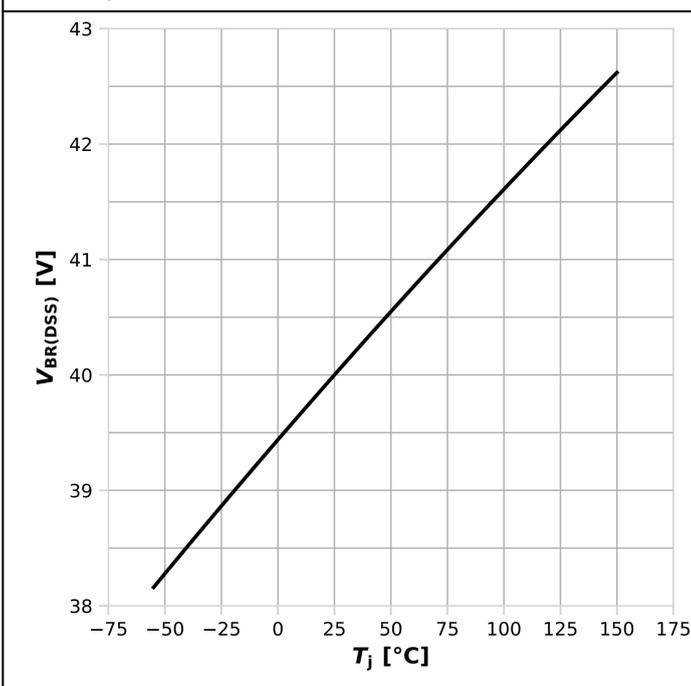
$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$ ; parameter:  $T_{j,start}$

Diagram 14: Typ. gate charge (n-channel)



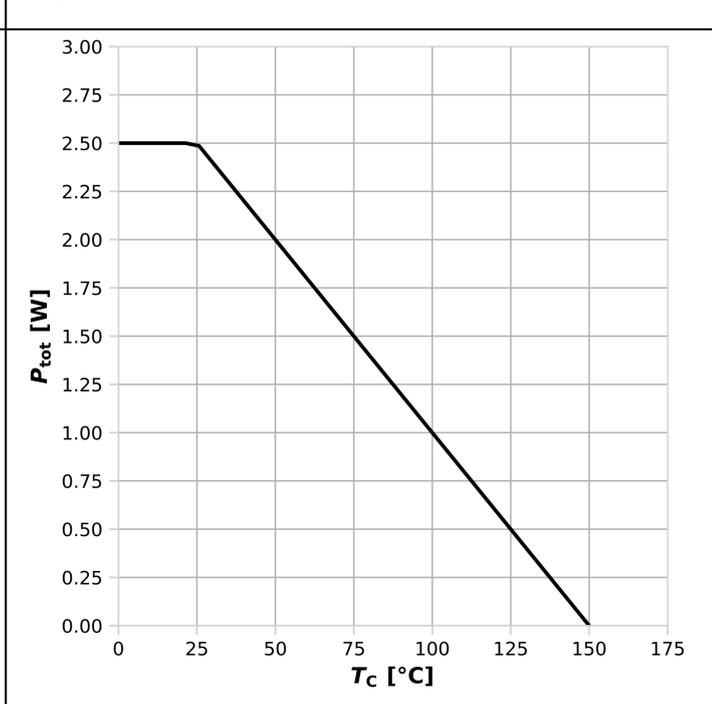
$V_{GS}=f(Q_{gate}), I_D=9.6$  A pulsed,  $T_j=25$  °C; parameter:  $V_{DD}$

Diagram 15: Drain-source breakdown voltage (n-channel)



$V_{BR(DSS)}=f(T_j); I_D=1$  mA

Diagram 16: Power dissipation (p-channel)



$P_{tot}=f(T_C)$

**Public**

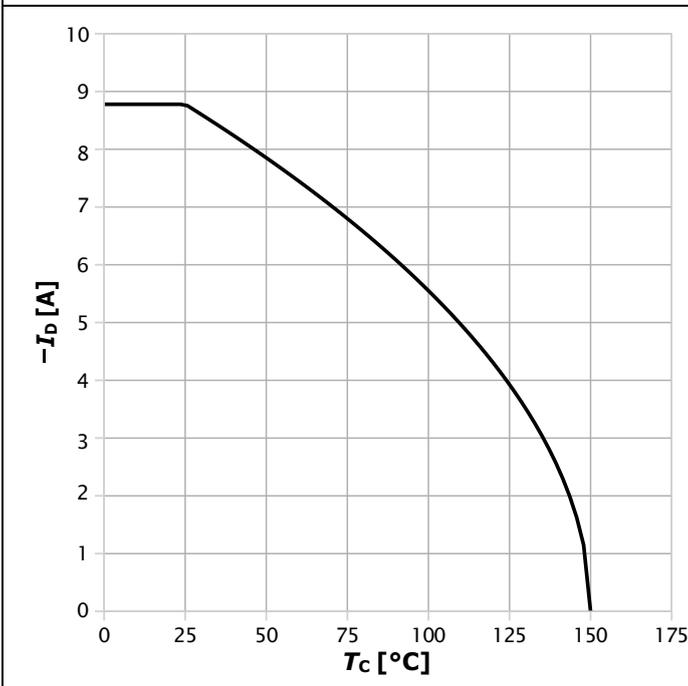
# OptiMOS™ 3 Power-Transistors, 40V

ISA170230C04LMDS

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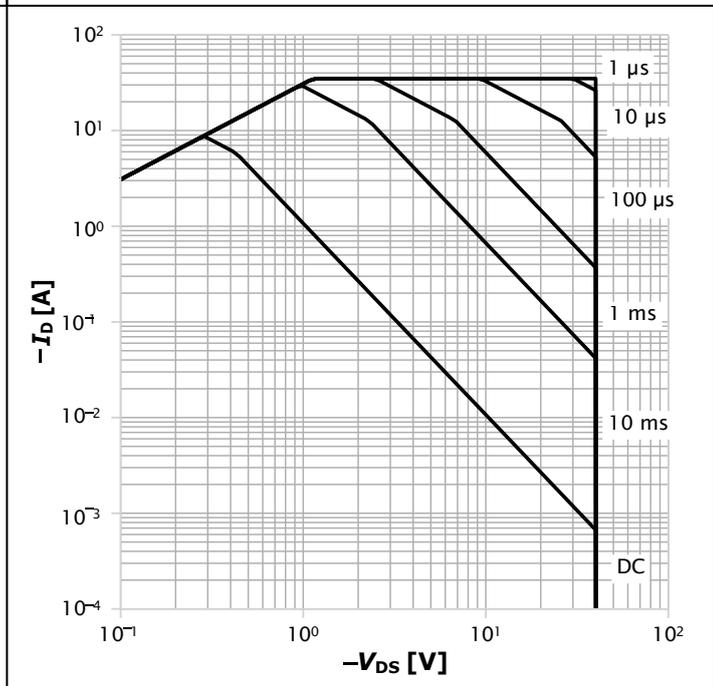


Diagram 17: Drain current (p-channel)



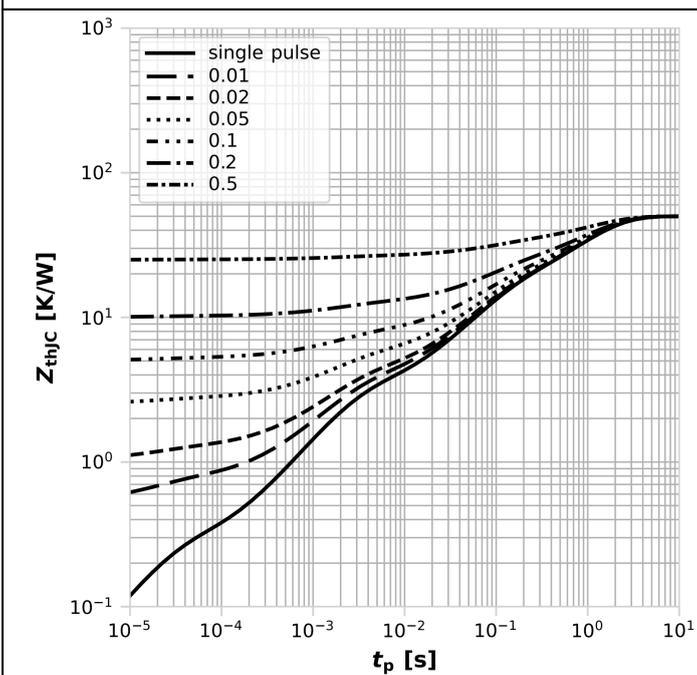
$I_b=f(T_c); |V_{GS}|\geq 10\text{ V}$

Diagram 18: Safe operating area (p-channel)



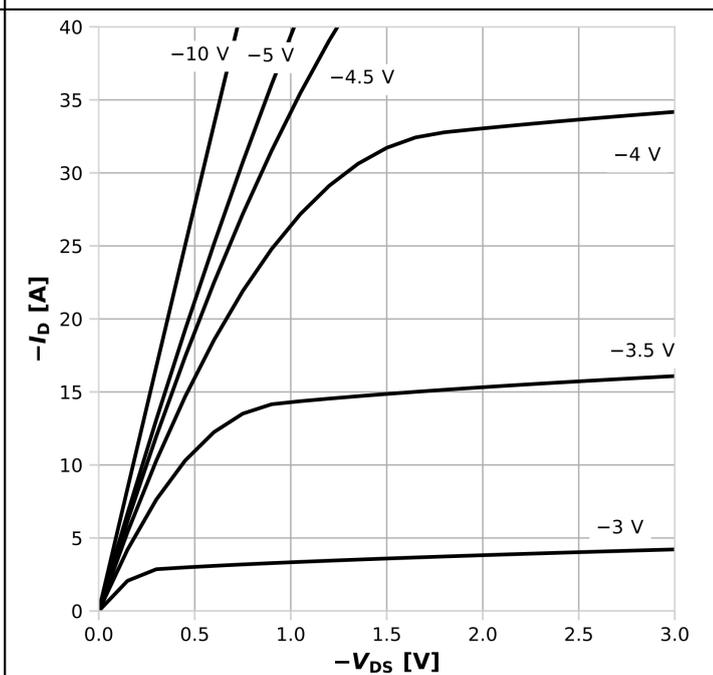
$I_b=f(V_{DS}); T_c=25\text{ °C}; D=0; \text{parameter: } t_p$

Diagram 19: Max. transient thermal impedance (p-channel)



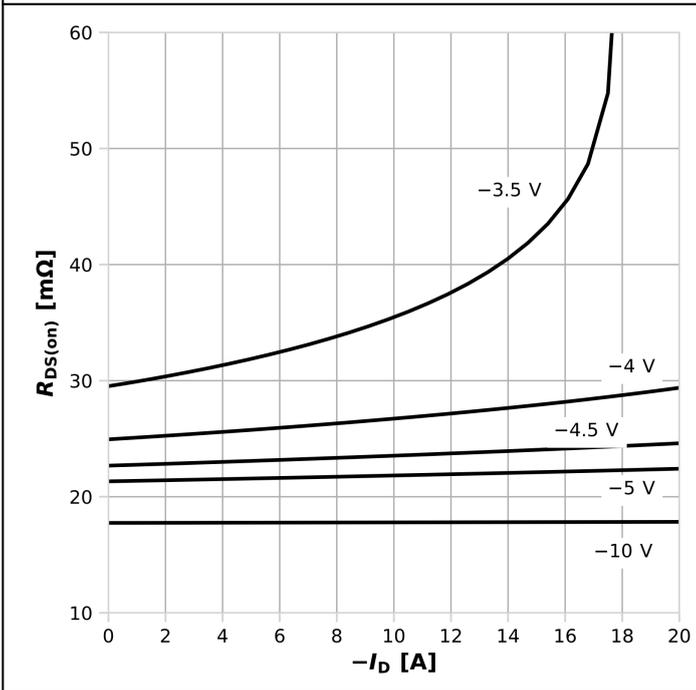
$Z_{thjc}=f(t_p); \text{parameter: } D=t_p/T$

Diagram 20: Typ. output characteristics (p-channel)



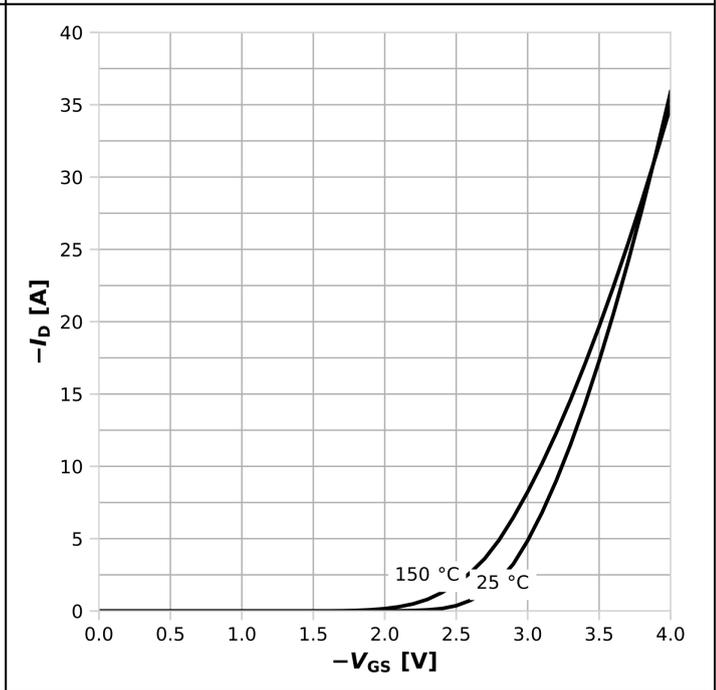
$I_b=f(V_{DS}), T_j=25\text{ °C}; \text{parameter: } V_{GS}$

Diagram 21: Typ. drain-source on resistance (p-channel)



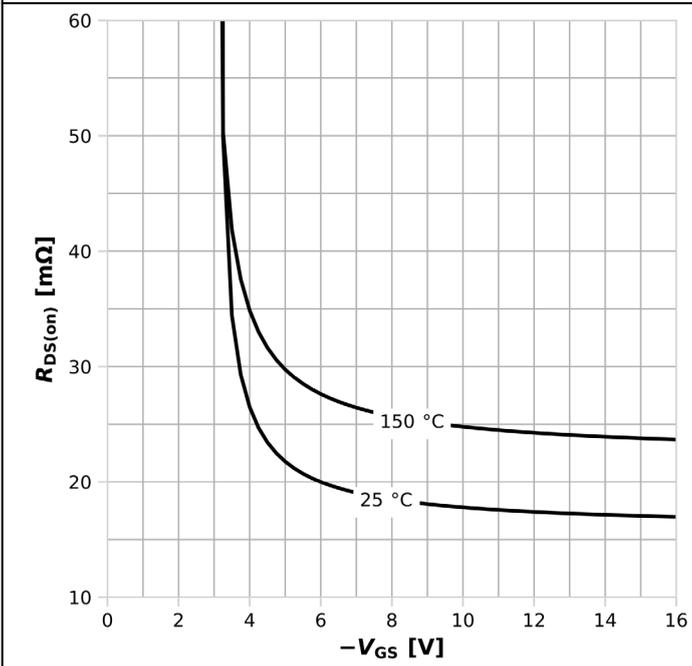
$R_{DS(on)} = f(I_D), T_j = 25\text{ }^\circ\text{C};$  parameter:  $V_{GS}$

Diagram 22: Typ. transfer characteristics (p-channel)



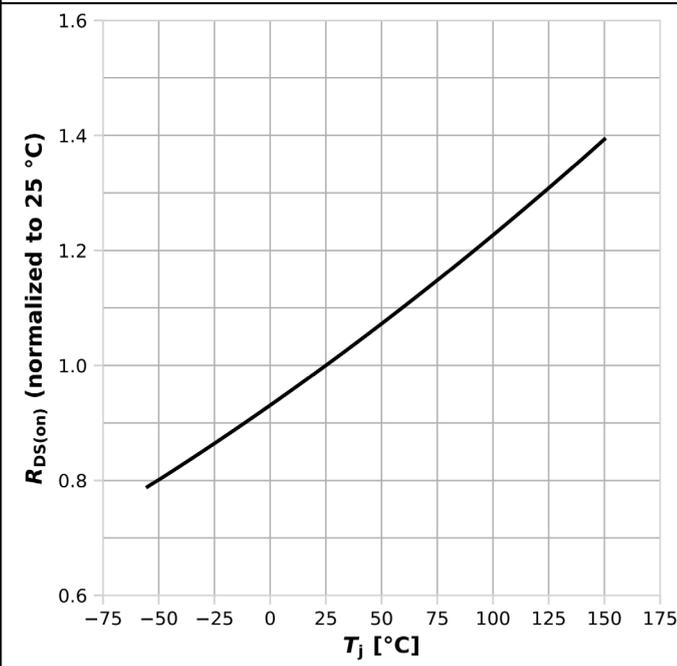
$I_D = f(V_{GS}), |V_{DS}| > 2|I_D|R_{DS(on)max};$  parameter:  $T_j$

Diagram 23: Typ. drain-source on resistance (p-channel)



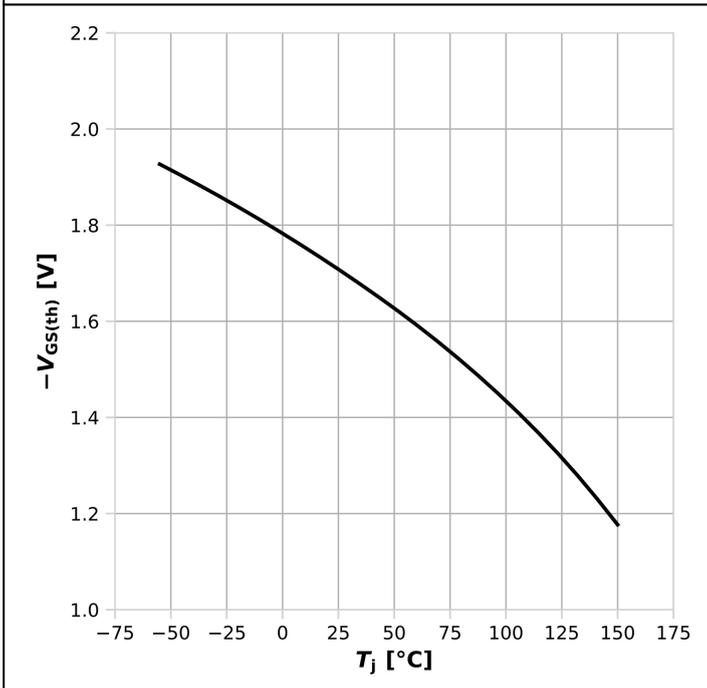
$R_{DS(on)}=f(V_{GS}), I_D=-8.8 \text{ A}; \text{parameter: } T_j$

Diagram 24: Normalized drain-source on resistance (p-ch.)



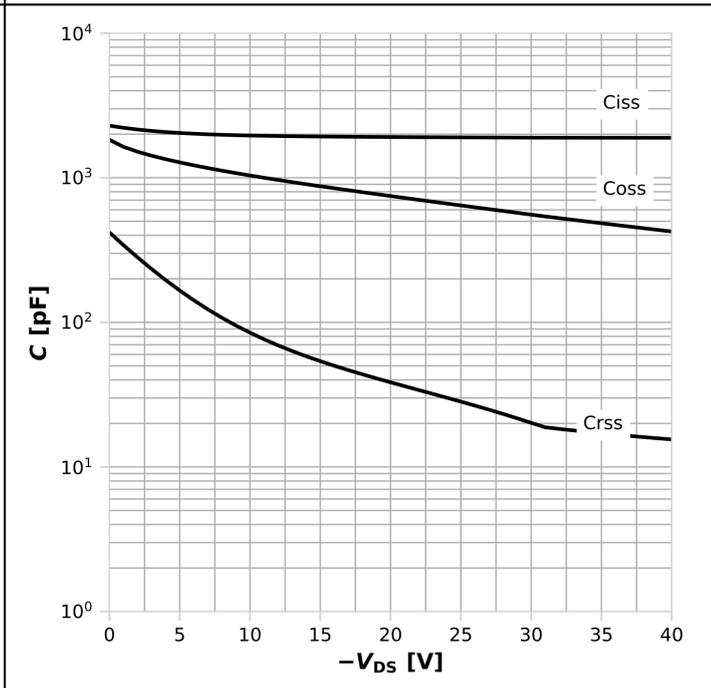
$R_{DS(on)}=f(T_j), I_D=-8.8 \text{ A}, V_{GS}=-10 \text{ V}$

Diagram 25: Typ. gate threshold voltage (p-channel)



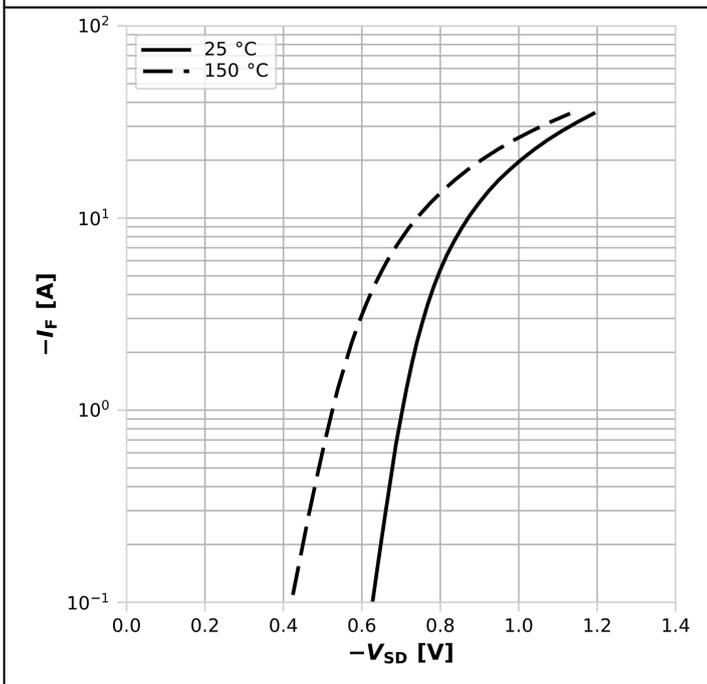
$V_{GS(th)}=f(T_j)$ ,  $V_{GS}=V_{DS}$ ; parameter:  $I_D=1000\mu A$

Diagram 26: Typ. capacitances (p-channel)



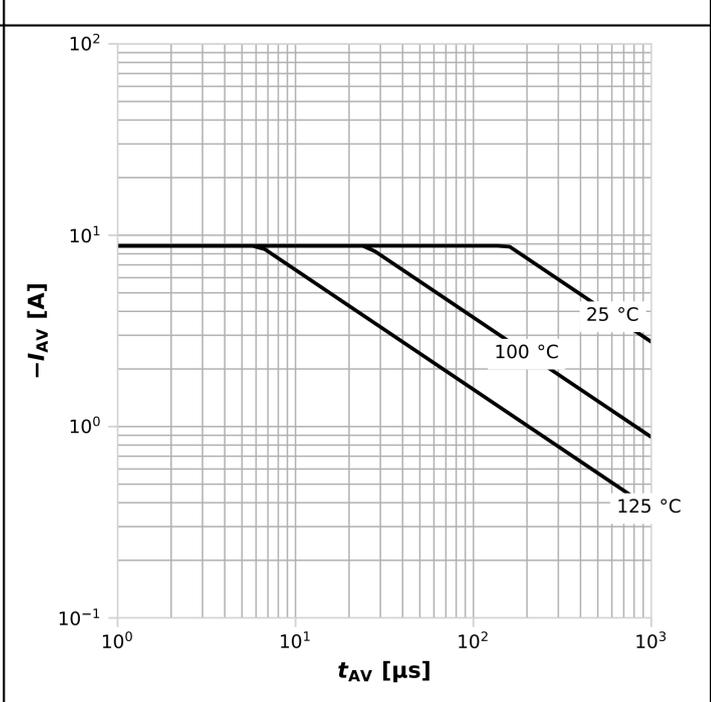
$C=f(V_{DS})$ ;  $V_{GS}=0 V$ ;  $f=1 MHz$

Diagram 27: Forward characteristics of reverse diode (p-ch.)

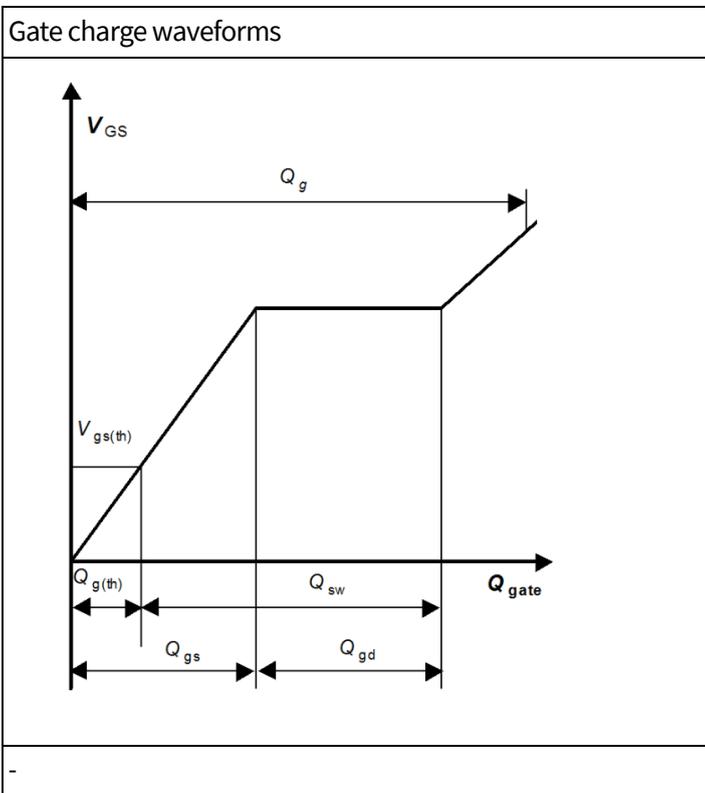
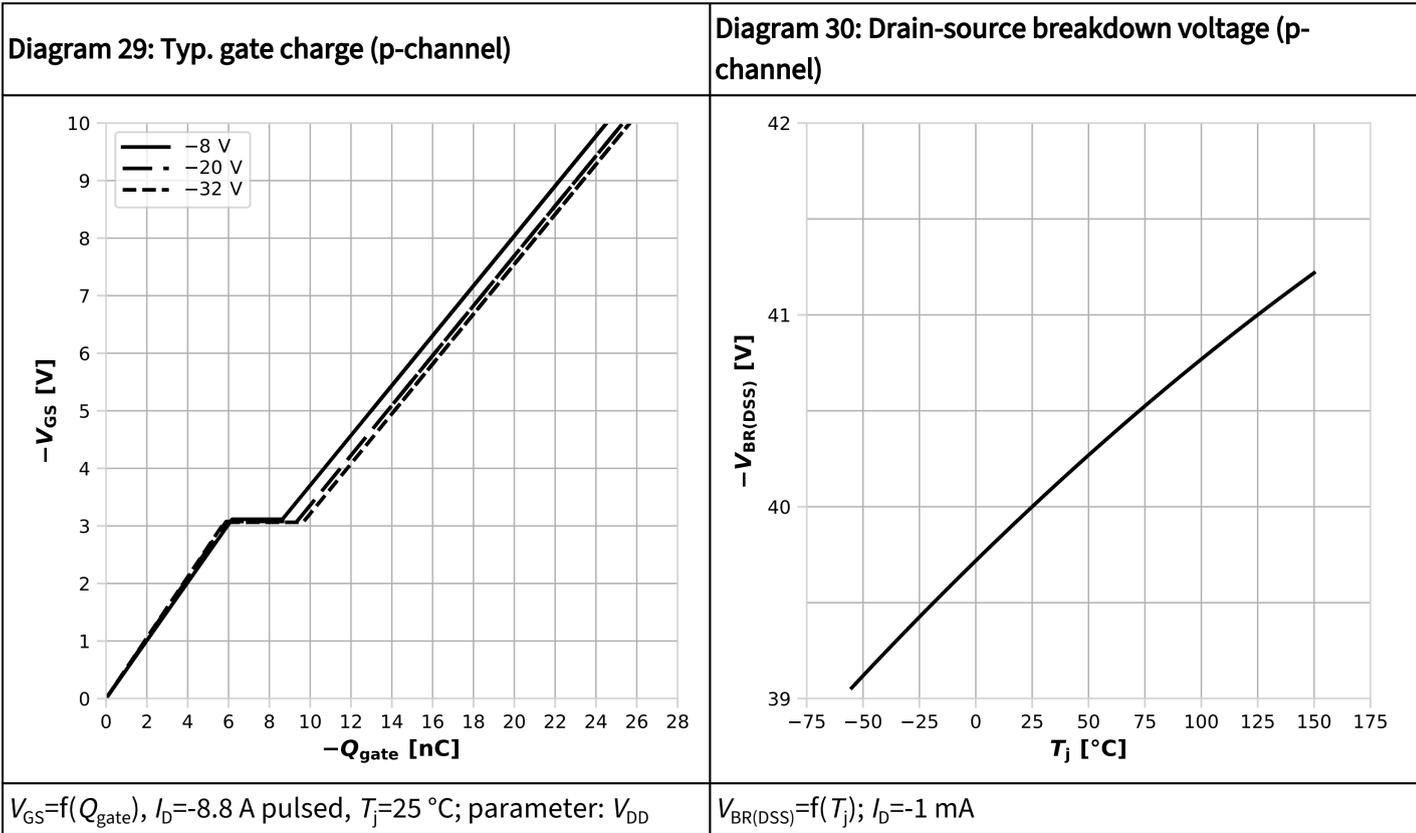


$I_F=f(V_{SD})$ ; parameter:  $T_j$

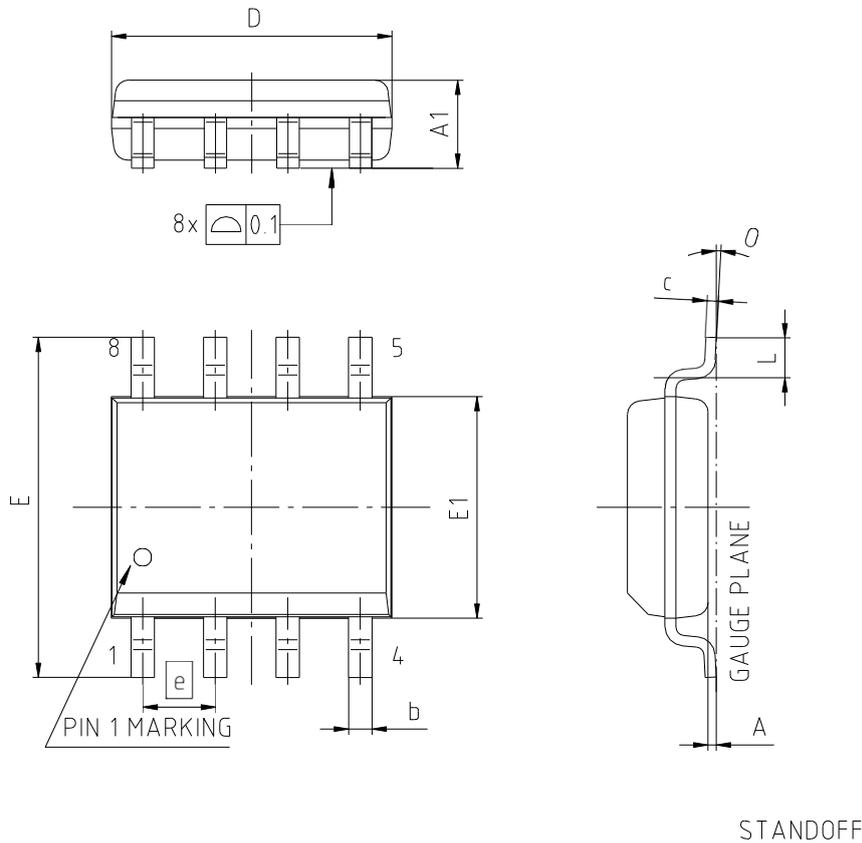
Diagram 28: Avalanche characteristics (p-channel)



$I_{AS}=f(t_{AV})$ ;  $R_{GS}=25 \Omega$ ; parameter:  $T_{j,start}$



## 5 封装外形



PACKAGE - GROUP NUMBER:		PG-DSO-8-U02	
DIMENSIONS	MILLIMETERS		
	MIN.	MAX.	
A	0.18	0.25	
A1	1.35	1.75	
b	0.38	0.51	
c	0.254		
D	4.80	5.00	
E	5.80	6.20	
E1	3.80	4.00	
e	1.27		
L	0.48	0.91	
O	4°		
N	8		

NOTE:  
DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS

图 1 PG-DSO-8 外形图，尺寸单位为毫米



修订记录

ISA170230C04LMDS

Revision 2024 - 10 - 02 , Rev. 2 . 0

历史修订版本

Revision	Date	Subjects (major changes since last revision)
2.0	2024-10-02	Release of final datasheet

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